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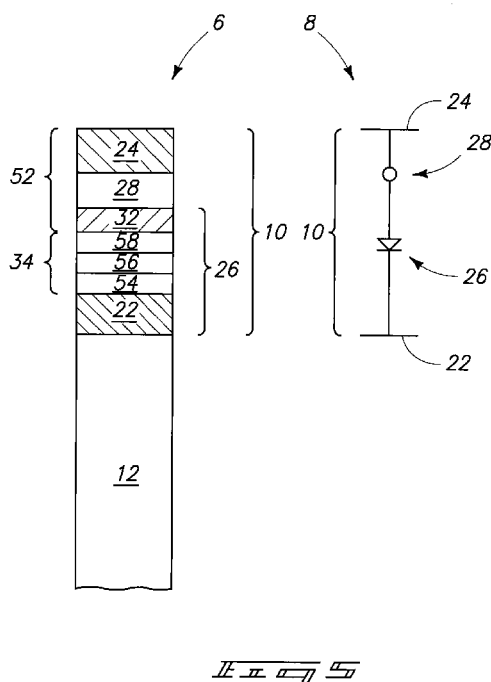
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(54) **Title:** MEMORY CELLS, MEMORY CELL CONSTRUCTIONS AND MEMORY CELL PROGRAMMING METHODS



(57) **Abstract:** Some embodiments include memory cells including a memory component having a first conductive material, a second conductive material, and an oxide material between the first conductive material and the second conductive material. A resistance of the memory component is configurable via a current conducted from the first conductive material through the oxide material to the second conductive material. Other embodiments include a diode comprising metal and a dielectric material and a memory component connected in series with the diode. The memory component includes a magnetoresistive material and has a resistance that is changeable via a current conducted through the diode and the magnetoresistive material.